

AMENDMENTS TO THE CLAIMS

Claims 1-29 (canceled)

30. (Presently Amended) A blocked metal silicide resistor structure, comprising:

a silicide blocking region comprising a silicon nitride film arranged over a region of doped polycrystalline silicon or doped silicon, wherein the silicon nitride film has [been] a conformality of greater than about 90%, and is formed by a rapid thermal nitride deposition process at a temperature from about 600 °C to about 775 °C;

[a region of a] metal silicide structures adjacent to opposite sides of the silicon nitride film[; and] with a contact overlying each of the adjacent silicide [regions] structures[;], wherein the resistor overlies device source/drain implants.

31. (canceled)

32. (original) The resistor structure according to claim 30, wherein the metal silicide is selected from the group consisting of titanium silicide and cobalt silicide.

33. (original) The resistor structure according to claim 30, wherein the silicon nitride film has a thickness of about 100 Å or less.

34. (original) The resistor structure according to claim 30, wherein the resistor structure is formed on cobalt silicide based structures.

35. (original) A bipolar transistor structure, comprising:

a nitride barrier layer formed by a rapid thermal chemical vapor deposition.

36. (canceled)